



**HARRIS  
INTEGRATED CIRCUITS  
MONOLITHIC  
DIODE MATRICES**

These devices are designed with the CMOS circuit engineer in mind, allowing the application of logically powerful programmable solutions to low power CMOS system applications.

They incorporate an advanced dielectric isolation process to eliminate the need for power supply pins and allow parasitic free operation.

**MAXIMUM RATINGS**

Rating	Value	Unit
Surge Current (100 $\mu$ s Max.)	200	mA
Total Circuit Dissipation (Still Air)	450	mW
Storage Temperature Range	-65 to +150	$^{\circ}$ C
Operating Temperature Range	-55 to +125	$^{\circ}$ C

**PACKAGING AVAILABLE**

(See page 87):

**C - 14-LEAD DUAL INLINE**

**V - 18-LEAD DUAL INLINE**

**D - 14-LEAD FLAT PACK**

FUNCTION	TYPE/PKG	FORWARD CURRENT	REVERSE BREAKDOWN VOLTAGE(min)
6 X 8 Diode Matrix	0168/C,D	100	30
8 X 6 Diode Matrix	0186/C,D	100	30
4 X 10 Diode Matrix	0410/C,D	100	30
10 X 4 Diode Matrix	0104/C,D	100	30
9 x 8 Diode Matrix	0198/V	100	30